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FAIRCHILD SEMICONDUCTOR®

March 2013

# FQPF22P10

## P-Channel QFET® MOSFET

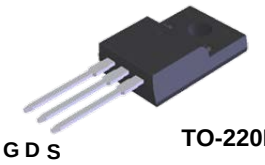
### -100 V, -13.2 A, 125 mΩ

### Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### Features

- -13.2 A, -100 V, $R_{DS(on)}$=125 mΩ(Max.) @$V_{GS}$=-10 V, $I_D$=-6.6 A
- Low Gate Charge (Typ. 40 nC)
- Low Crss (Typ. 160 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating

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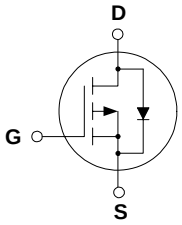



## Absolute Maximum Ratings

$T_C$ = 25°C unless otherwise noted

| Symbol | Parameter | | FQPF22P10 | Unit |
|---|---|---|---|---|
| $V_{DSS}$ | Drain-Source Voltage | | -100 | V |
| $I_D$ | Drain Current - Continuous ($T_C$ = 25°C) | | -13.2 | A |
| | Drain Current - Continuous ($T_C$ = 100°C) | | -9.3 | A |
| $I_{DM}$ | Drain Current - Pulsed | (Note 1) | -52.8 | A |
| $V_{GSS}$ | Gate-Source Voltage | | ± 30 | V |
| $E_{AS}$ | Single Pulsed Avalanche Energy | (Note 2) | 710 | mJ |
| $I_{AR}$ | Avalanche Current | (Note 1) | -13.2 | A |
| $E_{AR}$ | Repetitive Avalanche Energy | (Note 1) | 4.5 | mJ |
| dv/dt | Peak Diode Recovery dv/dt | (Note 3) | -6.0 | V/ns |
| $P_D$ | Power Dissipation ($T_C$ = 25°C) | | 45 | W |
| | - Derate above 25°C | | 0.3 | W/°C |
| $T_J$, $T_{STG}$ | Operating and Storage Temperature Range | | -55 to +175 | °C |
| $T_L$ | Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds | | 300 | °C |

## Thermal Characteristics

| Symbol | Parameter | Typ | Max | Unit |
|---|---|---|---|---|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case | -- | 3.3 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | -- | 62.5 | °C/W |

## Electrical Characteristics

$T_C$ = 25°C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Off Characteristics** | | | | | | |
| $BV_{DSS}$ | Drain-Source Breakdown Voltage | $V_{GS}$ = 0 V, $I_D$ = -250 μA | -100 | -- | -- | V |
| $\Delta BV_{DSS}$ / $\Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D$ = -250 μA, Referenced to 25°C | -- | -0.1 | -- | V/°C |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = -100 V, $V_{GS}$ = 0 V | -- | -- | -1 | μA |
| | | $V_{DS}$ = -80 V, $T_C$ = 125°C | -- | -- | -10 | μA |
| $I_{GSSF}$ | Gate-Body Leakage Current, Forward | $V_{GS}$ = -30 V, $V_{DS}$ = 0 V | -- | -- | -100 | nA |
| $I_{GSSR}$ | Gate-Body Leakage Current, Reverse | $V_{GS}$ = 30 V, $V_{DS}$ = 0 V | -- | -- | 100 | nA |
| **On Characteristics** | | | | | | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$ = $V_{GS}$, $I_D$ = -250 μA | -2.0 | -- | -4.0 | V |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance | $V_{GS}$ = -10 V, $I_D$ = -6.6 A | -- | 0.096 | 0.125 | Ω |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$ = -40 V, $I_D$ = -6.6 A (Note 4) | -- | 11 | -- | S |
| **Dynamic Characteristics** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = -25 V, $V_{GS}$ = 0 V, f = 1.0 MHz | -- | 1170 | 1500 | pF |
| $C_{oss}$ | Output Capacitance | | -- | 460 | 600 | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | -- | 160 | 200 | pF |
| **Switching Characteristics** | | | | | | |
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD}$ = -50 V, $I_D$ = -22 A, $R_G$ = 25 Ω (Note 4, 5) | -- | 17 | 45 | ns |
| $t_r$ | Turn-On Rise Time | | -- | 170 | 350 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | -- | 60 | 130 | ns |
| $t_f$ | Turn-Off Fall Time | | -- | 110 | 230 | ns |
| $Q_g$ | Total Gate Charge | $V_{DS}$ = -80 V, $I_D$ = -22 A, $V_{GS}$ = -10 V (Note 4, 5) | -- | 40 | 50 | nC |
| $Q_{gs}$ | Gate-Source Charge | | -- | 7.0 | -- | nC |
| $Q_{gd}$ | Gate-Drain Charge | | -- | 21 | -- | nC |
| **Drain-Source Diode Characteristics and Maximum Ratings** | | | | | | |
| $I_S$ | Maximum Continuous Drain-Source Diode Forward Current | | -- | -- | -13.2 | A |
| $I_{SM}$ | Maximum Pulsed Drain-Source Diode Forward Current | | -- | -- | -52.8 | A |
| $V_{SD}$ | Drain-Source Diode Forward Voltage | $V_{GS}$ = 0 V, $I_S$ = -13.2 A | -- | -- | -4.0 | V |
| $t_{rr}$ | Reverse Recovery Time | $V_{GS}$ = 0 V, $I_S$ = -22 A, $dI_F$ / dt = 100 A/μs (Note 4) | -- | 110 | -- | ns |
| $Q_{rr}$ | Reverse Recovery Charge | | -- | 0.6 | -- | μC |

**Notes:**
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 6.1mH, $I_{AS}$ = -13.2A, $V_{DD}$ = -25V, $R_G$ = 25 Ω, Starting $T_J$ = 25°C
3. $I_{SD}$ ≤ -22A, di/dt ≤ 300A/μs, $V_{DD}$ ≤ $BV_{DSS}$, Starting $T_J$ = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

## Typical Characteristics

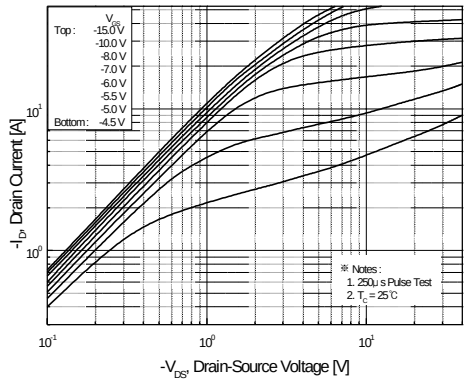



**Figure 1. On-Region Characteristics**

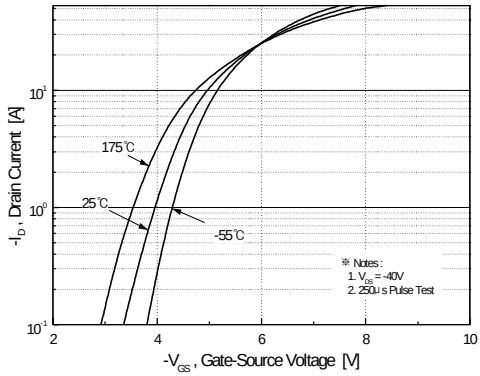



**Figure 2. Transfer Characteristics**

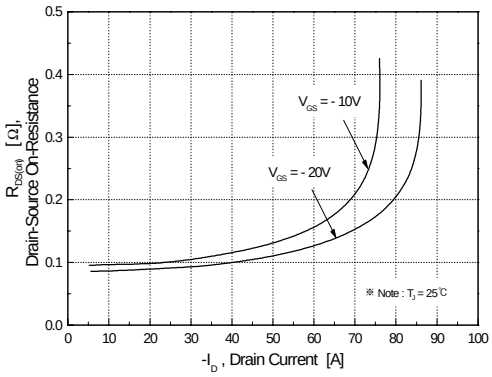



**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**

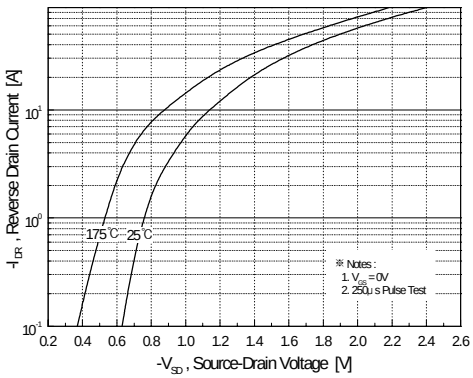



**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**

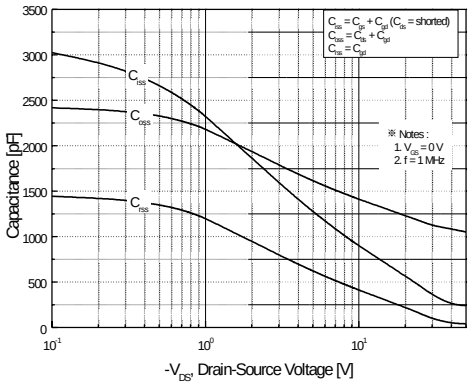



**Figure 5. Capacitance Characteristics**

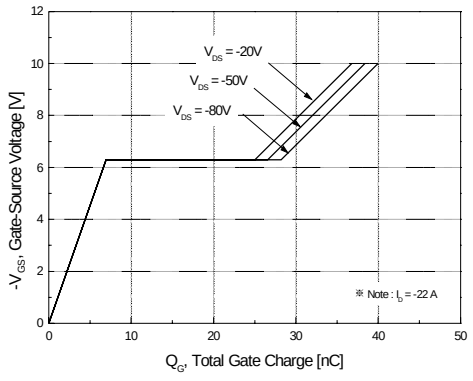



**Figure 6. Gate Charge Characteristics**

## Typical Characteristics (Continued)

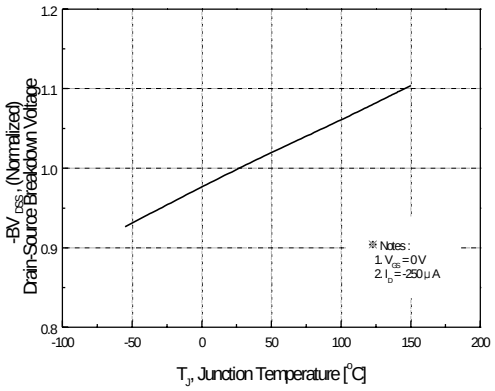



**Figure 7. Breakdown Voltage Variation vs. Temperature**

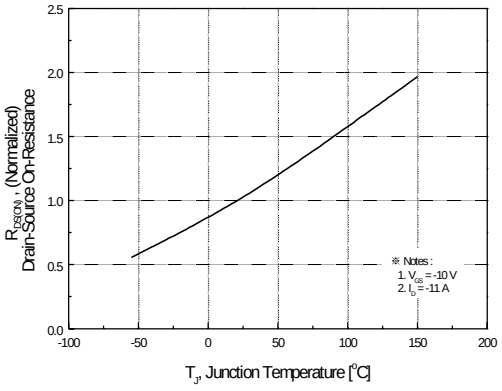



**Figure 8. On-Resistance Variation vs. Temperature**

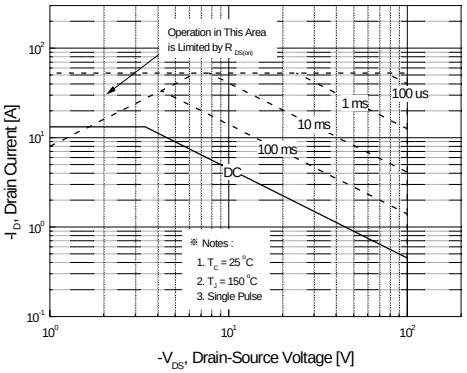



**Figure 9. Maximum Safe Operating Area**

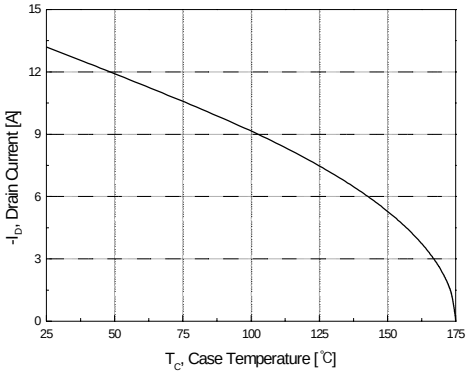



**Figure 10. Maximum Drain Current vs. Case Temperature**

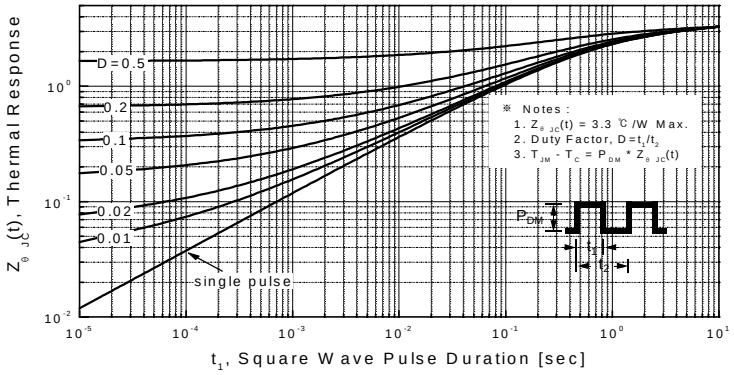
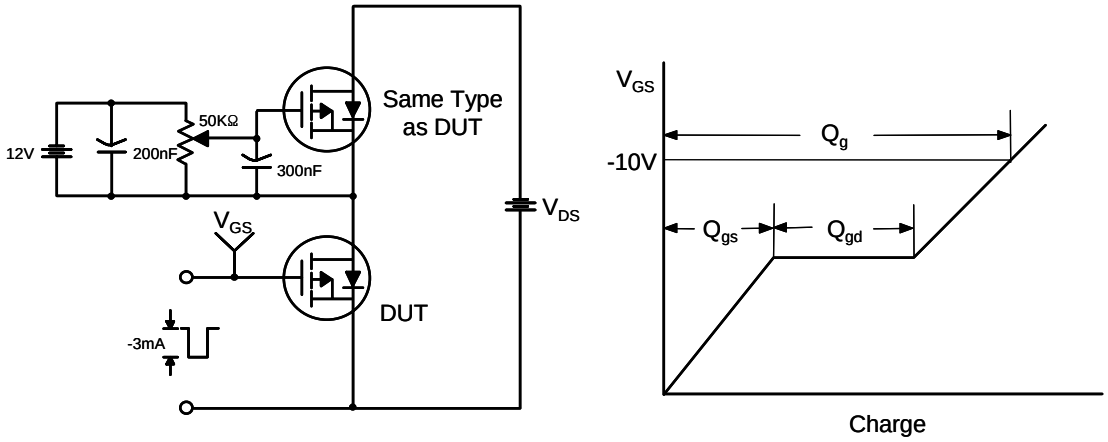
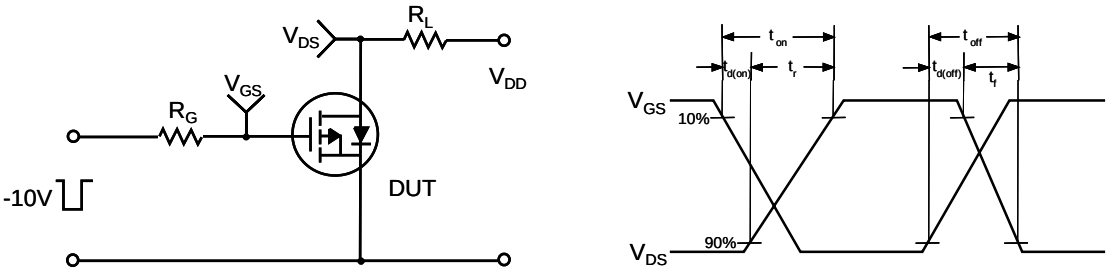



**Figure 11. Transient Thermal Response Curve**

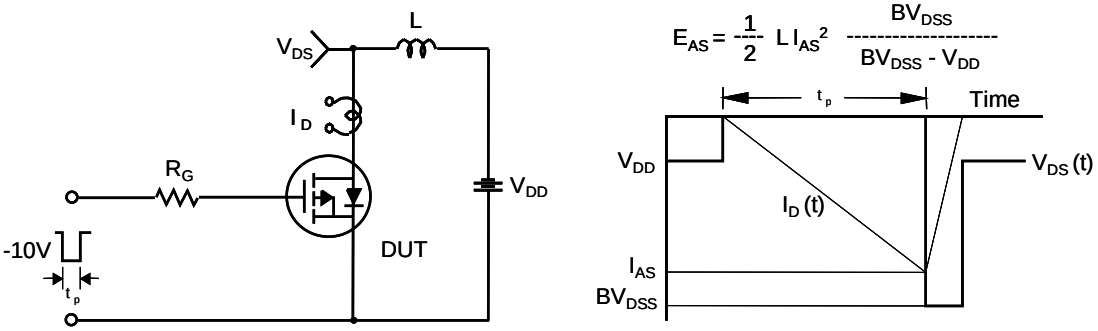
**Gate Charge Test Circuit & Waveform**



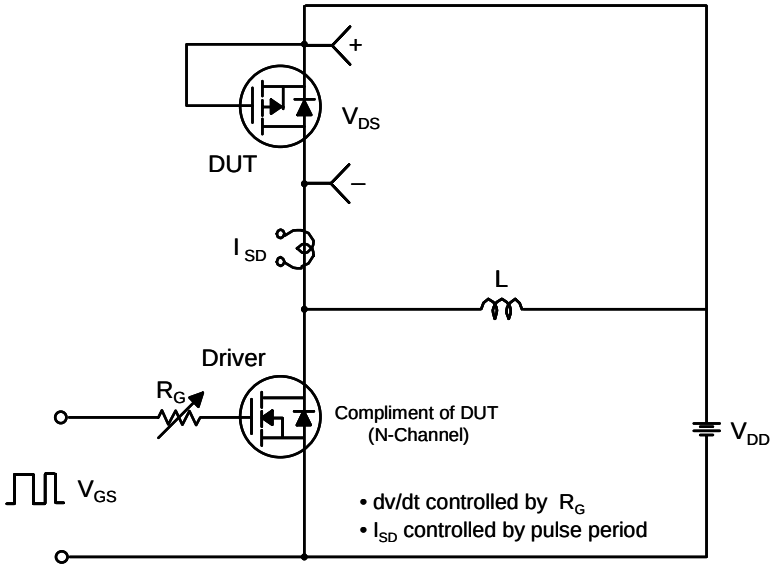

**Resistive Switching Test Circuit & Waveforms**

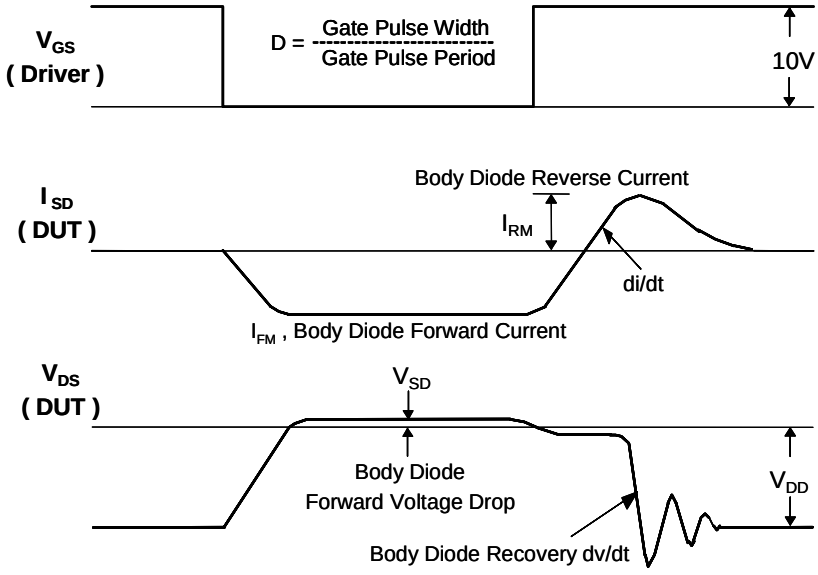



**Unclamped Inductive Switching Test Circuit & Waveforms**



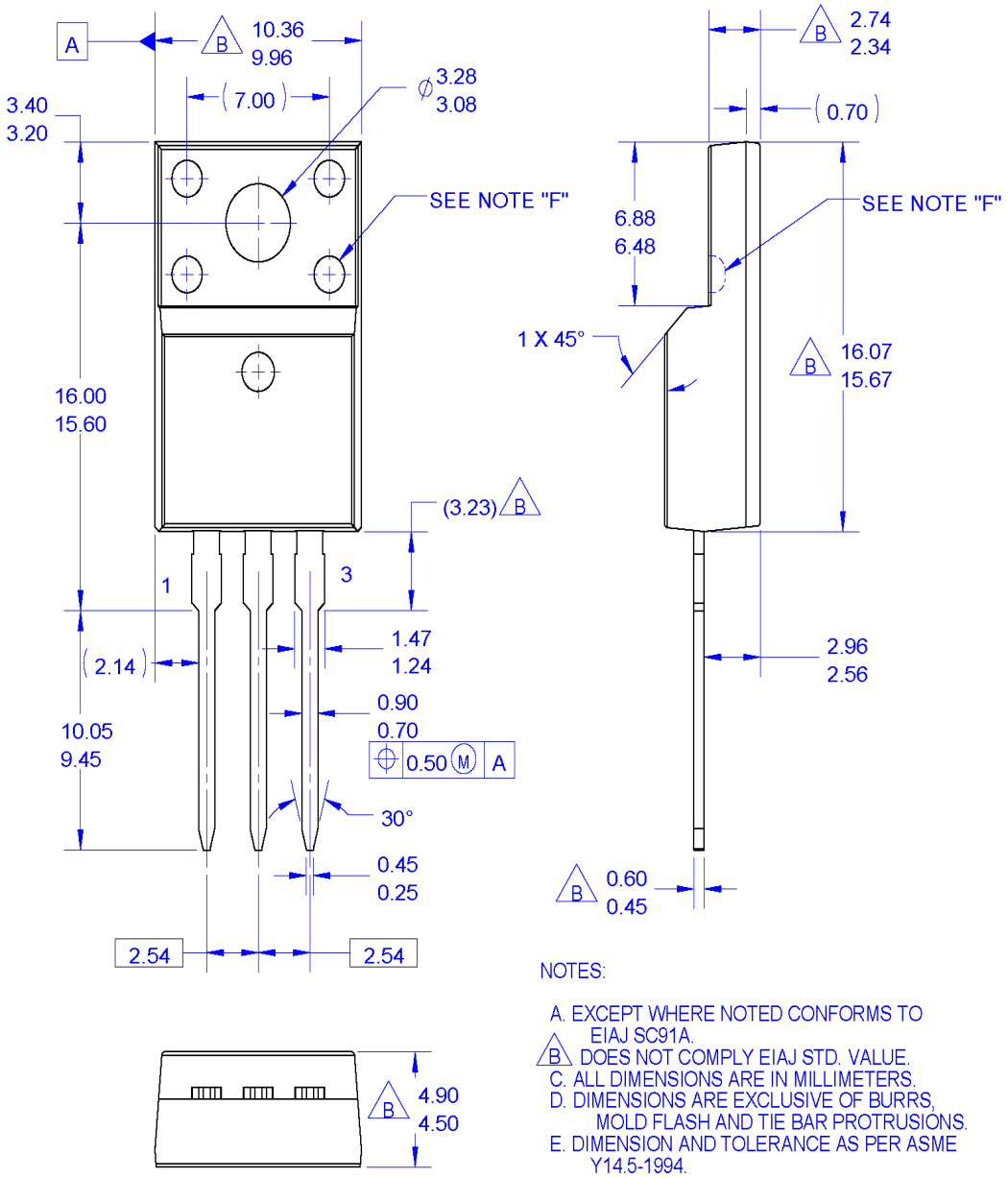
**Peak Diode Recovery dv/dt Test Circuit & Waveforms**



## Mechanical Dimensions

# TO-220F




NOTES:

A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
B DOES NOT COMPLY EIAJ STD. VALUE.
C. ALL DIMENSIONS ARE IN MILLIMETERS.
D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
F. OPTION 1 - WITH SUPPORT PIN HOLE.
OPTION 2 - NO SUPPORT PIN HOLE.
G. DRAWING FILE NAME: TO220M03REV3

Dimensions in Millimeters

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